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NXPS20H100C



Dual power Schottky diode Rev. 2 — 8 June 2012

Product data sheet

Product profile 1.

1.1 General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- High junction temperature capability
- Low leakage current

- Negligible switching losses
- Optimised design to give low V_F and high T_{j(max)}

1.3 Applications

- DC to DC converters
- Freewheeling diode

- OR-ing diode
- Switched mode power supply rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	100	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5; $T_{mb} \le 163$ °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	Α
$I_{O(AV)}$	average output current	square-wave pulse; $\delta = 0.5$; $T_{mb} \le 161$ °C; both diodes conducting	-	-	20	Α
Tj	junction temperature		-	-	175	°C
Static charac	eteristics					
V_{F}	forward voltage	I _F = 10 A; T _j = 25 °C; see <u>Figure 6</u>	-	-	0.77	V
		I _F = 10 A; T _j = 125 °C; see <u>Figure 6</u>	-	0.59	0.64	V
I _R	reverse current	$V_R = 100 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
		V _R = 100 V; T _j = 125 °C; see <u>Figure 7</u>	-	1	6	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1 + H A2
3	A2	anode 2		<u> </u>
mb	К	mounting base; cathode		sym125
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NXPS20H100C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	100	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5; $T_{mb} \le 163$ °C; per diode; see Figure 1; see Figure 2; see Figure 3	-	10	Α
I _{O(AV)}	average output current	square-wave pulse; $\delta = 0.5$; $T_{mb} \le 161$ °C; both diodes conducting	-	20	Α
I _{FSM}	non-repetitive peak forward current	sine-wave pulse; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; see Figure 4	-	250	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

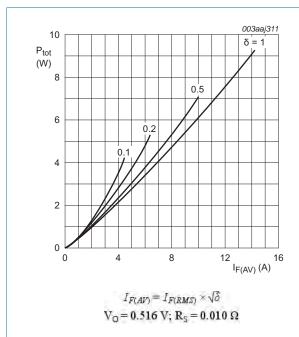


Fig 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

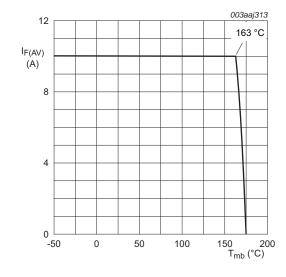


Fig 3. Average forward current as a function of mounting base temperature; per diode; maximum values

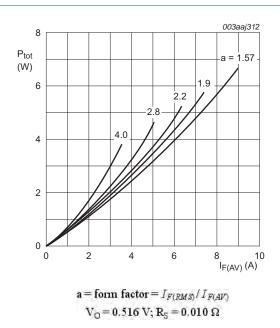


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

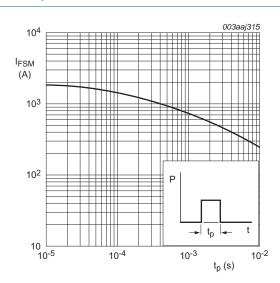


Fig 4. Non-repetitive peak forward current as a function of pulse width; square waveform; per diode; maximum values

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 5	-	-	1.6	K/W
		with heatsink compound; both diodes conducting	-	-	0.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

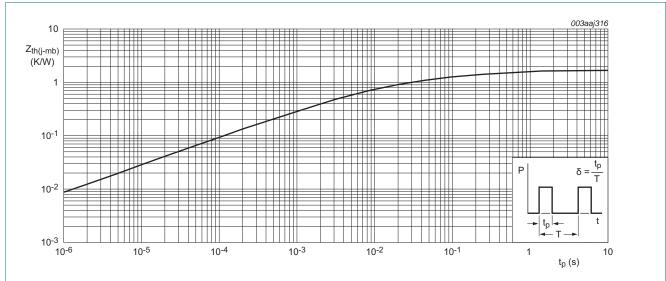
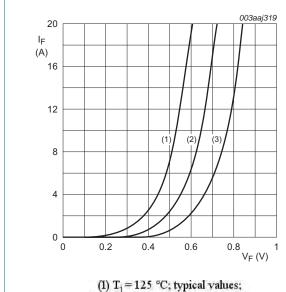


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width; per diode

Characteristics

Table 6. **Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F forv	forward voltage	$I_F = 8 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 6	-	-	0.71	V
		I _F = 10 A; T _j = 25 °C; see <u>Figure 6</u>	-	-	0.77	V
		I _F = 16 A; T _j = 25 °C; see <u>Figure 6</u>	-	-	0.81	V
		I _F = 20 A; T _j = 25 °C; see <u>Figure 6</u>	-	-	0.88	V
		I _F = 8 A; T _j = 125 °C; see <u>Figure 6</u>	-	0.56	0.58	V
		I _F = 10 A; T _j = 125 °C; see <u>Figure 6</u>	-	0.59	0.64	V
		I _F = 16 A; T _j = 125 °C; see <u>Figure 6</u>	-	0.65	0.68	V
		I _F = 20 A; T _j = 125 °C; see <u>Figure 6</u>	-	0.67	0.73	V
I _R	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	1	6	mΑ
Dynamic ch	naracteristics					
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 10 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 8	-	250	-	pF

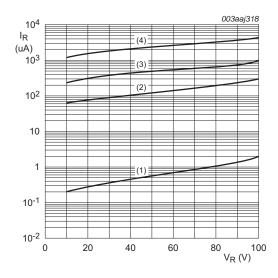


(2) T_i = 125 °C; maximum values;

(3) T₁=25 °C; maximum values;

 $V_O = 0.516 \text{ V}; R_S = 0.010 \Omega$

Fig 6. Forward current as a function of forward voltage; per diode



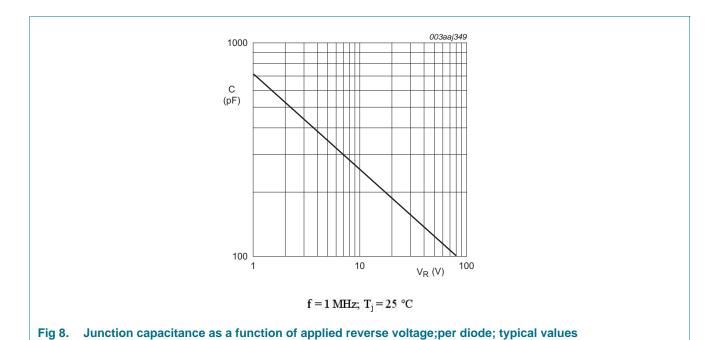
(1) T_j = 25 °C; typical values;

(2) T_i = 100 °C; typical values;

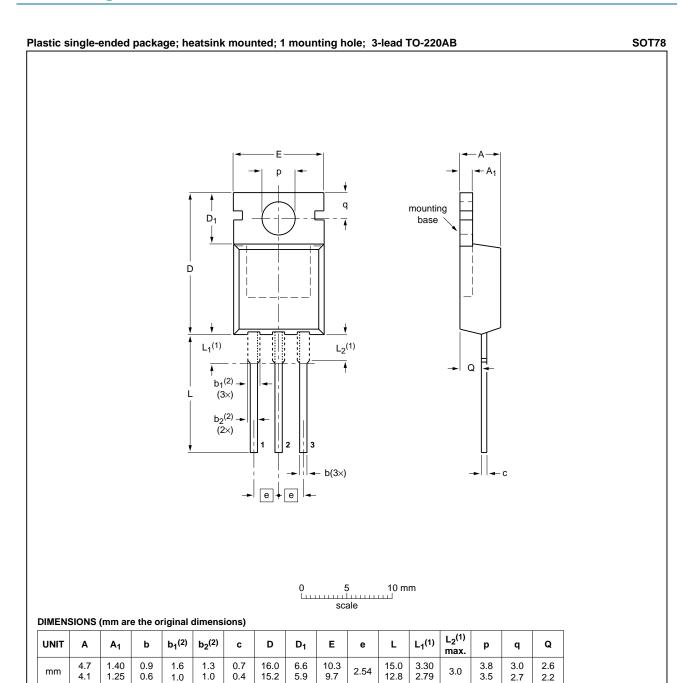
(3) T_i = 125 °C; typical values;

(4) T_j = 150 °C; typical values

Fig 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 9. Package outline SOT78 (TO-220AB)

NXPS20H100C

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXPS20H100C v.2	20120608	Product data sheet	-	NXPS20H100C v.1
Modifications:	 Status changed 	d from preliminary to produc	t.	
	 Various change 	es to content.		
NXPS20H100C v.1	20120420	Preliminary data shee	t -	-

9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Dual power Schottky diode

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